A rigorous computational framework employing coupled-mode theory for assessing lasing with transition metal dichalcogenide bilayers in the nanoscale <u>G. Nousios,^{1,*} T. Christopoulos,¹ D. C. Zografopoulos,² and E. E. Kriezis¹</u>

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$$\nabla \times \boldsymbol{\mathcal{E}}(\mathbf{r}, t) = -\mu_0 \frac{\partial \boldsymbol{\mathcal{H}}(\mathbf{r}, t)}{\partial t}$$
$$\nabla \times \boldsymbol{\mathcal{H}}(\mathbf{r}, t) = \varepsilon_0 \varepsilon_{\mathbf{r}} \frac{\partial \boldsymbol{\mathcal{E}}(\mathbf{r}, t)}{\partial t} + \left[\frac{\partial \boldsymbol{\mathcal{P}}_{||}(\mathbf{r}, t)}{\partial t} \delta_S(\mathbf{r}) \right]$$

$$\Delta \tilde{\omega}(t) = i\xi_1 \frac{1}{dt} \left[i\omega_n n(t) + \frac{\mathrm{d}p(t)}{dt} \right] \qquad \xi_1 = 0$$

$$\xi_1 = \frac{1}{4} \iint |\mathbf{E}_{\text{ref},\parallel}|^2 \mathrm{d}S$$

$$\frac{\mathrm{d}a(t)}{\mathrm{d}t} = -j(\omega_{\mathrm{ref}} - \omega_c)a(t) - \frac{1}{\tau_\ell}a(t) + j\Delta\tilde{\omega}(t)a(t)$$

$$\frac{\partial^2 \mathcal{P}_{||}(\mathbf{r},t)}{\partial t^2} + \Gamma_m \frac{\partial \mathcal{P}_{||}(\mathbf{r},t)}{\partial t} + \omega_m^2 \mathcal{P}_{||}(\mathbf{r},t) = -\sigma_m \Delta N_s(\mathbf{r},t) \mathcal{E}_{||}(\mathbf{r},t)$$

5. It is introduced in the CMT framework by exploiting the **slowly-varying** envelope approximation (SVEA).

$$\frac{\mathrm{d}p(t)}{\mathrm{d}t} = -\frac{\omega_m^2 - \omega_{\mathrm{ref}}^2 + j\omega_{\mathrm{ref}}\Gamma_m}{\Gamma_m + j2\omega_{\mathrm{ref}}}p(t) - \frac{\sigma_m}{\Gamma_m + j2\omega_{\mathrm{ref}}}\Delta\bar{N}_s(t)a(t)$$

6. The carrier dynamics are described by semiclassical carrier rate equations.

$$\frac{\mathrm{d}\bar{N}_{2,s}(t)}{\mathrm{d}t} = \frac{\xi_2}{2\hbar\omega_m} \operatorname{Re}\left\{\left[j\omega_{\mathrm{ref}}p(t) + \frac{\mathrm{d}p(t)}{\mathrm{d}t}\right]a^*(t)\right\} - \frac{\bar{N}_{2,s}(t)}{\tau_{21}} + \frac{\bar{N}_{3,s}(t)}{\tau_{32}}\right\}$$

For a **three-level** gain medium the framework consists of **five** first-order **ODEs** (cavity amplitude, $\xi_2 =$ polarization and three carrier rate equations).



- Greater WGM mode order (greater radius R of the disk resonator) results in improvement of both lasing threshold and output power.
- The **height of the resonator** affects the **absorption efficiency** of the pumping power, η_p , due to the formation of a vertical Fabry-Pérot cavity when the structure is pumped. η_p maximizes for h = 330 nm leading to lowest lasing threshold and maximum output power.

$P_{p,\text{th}} = 1.3 \text{ mW}$ $\Delta \overline{N}_{\text{th}} = 4.61 \text{x} 10^{10} \text{ cm}^{-2}$			$R = 1.317 \ \mu m$		
			h = 330 nm		
			g = 300 nm		
$Q_i = 101\ 500$	$Q_{e} = 9600$	$\eta_p = 8.6 \%$	ξ_1 =	$= 8.93 \times 10^{15} \text{V/C}$	$\xi_2 = 1.29 \text{x} 10^{28} \text{V/(Cm^2)}$

Conclusion



The MoS₂/WSe₂ TMD hetero-bilayer



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A rigorous framework based on temporal CMT and perturbation theory has been presented capable of treating contemporary **2D gain materials** and accurately evaluating fundamental lasing characteristics of micro/nano-cavity lasers. Utilizing the framework, a **practical laser element** consisting of a SRNOI disk resonator with the gain provided by a MoS_2/WSe_2 hetero-bilayer has been designed, exhibiting low lasing threshold at a pump of 1.3 mW.

References

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